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DGSS 10-06CC

Gallium Arsenide Schottky Rectifier

Second generation

ISOPLUS220™

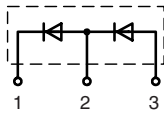
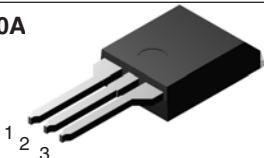
Electrically Isolated Back Surface

Preliminary Data

$$V_{RRM} = 600 \text{ V (2x300V)}$$

$$I_{DC} = 25 \text{ A}$$

$$C_{Junction} = 10.7 \text{ pF}$$

Type	Marking on product	Circuit	Package
DGSS 10-06CC	DGSS 10-06CC		ISOPLUS220A 

Diode

Symbol	Conditions	Maximum Ratings	
$V_{RRM/RSM}$	(between terminal 1 and 3)	600	V
		300	V
I_{FAV}	$T_C = 25^\circ\text{C}; \text{DC}$	25	A
	$T_C = 90^\circ\text{C}; \text{DC}$	15	A
I_{FSM}	$T_{VJ} = 45^\circ\text{C}; t_p = 10 \text{ ms (50 Hz), sine}$	80	A
P_{tot}	$T_C = 25^\circ\text{C}$	29	W

Features

GaAs Schottky Diode with Enhanced Barrier Height:

- lowest operating forward voltage drop due to additional injection of minority carriers
- high switching speed
 - low junction capacity of GaAs diode independent from temperature
 - short and low reverse recovery current peak due to short lifetime of minority carriers
 - soft turn off
- low leakage current

ISOPLUS220™ Package:

- isolated back surface
- low coupling capacity between pins and heatsink
- enlarged creepage
- high reliability
- industry standard outline

Applications

Power Factor Correction (PFC) Switched Mode Power Supplies:

- AC-DC converters
- DC-DC converters

with:

- high switching frequency
 - high efficiency
 - low EMI
- for use e. g. in:*
- telecom
 - computer
 - automotive equipment

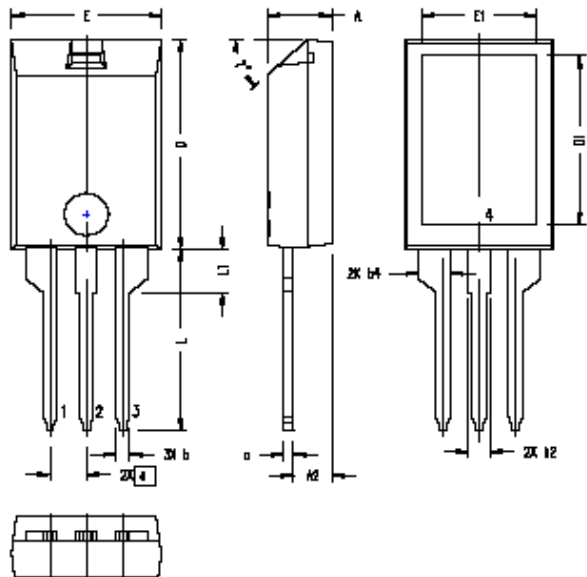
Symbol	Conditions	Characteristic Values		
		min.	typ.	max.
V_F	$I_F = 10 \text{ A}; T_{VJ} = 25^\circ\text{C}$	1.7	2.1	V
	$I_F = 10 \text{ A}; T_{VJ} = 125^\circ\text{C}$	1.2		V
I_R	$V_R = V_{RRM}; T_{VJ} = 25^\circ\text{C}$		0.25	mA
	$V_R = V_{RRM}; T_{VJ} = 125^\circ\text{C}$	25		μA
I_{RM}	$I_F = 5 \text{ A}; -di_F/dt = 150 \text{ A/}\mu\text{s};$ $V_R = 150 \text{ V}; T_{VJ} = 125^\circ\text{C}$	1.4		A
		23		ns
C_J	$V_R = 150 \text{ V}; T_{VJ} = 125^\circ\text{C}$	10.7		pF
R_{thJC}				5.2 KW

Data according to IEC 60747 and per diode unless otherwise specified

Component			
Symbol	Conditions	Maximum Ratings	
I_{RMS}	per pin	45	A
T_{VJ}		-55...+175	°C
T_{stg}		-55...+150	°C
V_{ISOL}	$I_{ISOL} \leq 1 \text{ mA}; 50/60 \text{ Hz}$	2500	V~
F_c	mounting force with clip	10...50	N

Symbol	Conditions	Characteristic Values		
		min.	typ.	max.
C_p	coupling capacity between shorted pins and mounting tab in the case		15	pF
R_{thcs}			0.3	K/W
Weight			2	g

ISOPLUS220 OUTLINE



SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.157	.197	4.00	5.00
A2	.098	.118	2.50	3.00
b	.035	.051	0.90	1.30
b2	.049	.065	1.25	1.65
b4	.093	.100	2.35	2.55
c	.028	.039	0.70	1.00
D	.591	.630	15.00	16.00
D1	.472	.512	12.00	13.00
E	.394	.433	10.00	11.00
E1	.295	.335	7.50	8.50
e	.100 BASIC		2.55 BASIC	
L	.512	.571	13.00	14.50
L1	.118	.138	3.00	3.50
T*			42.5'	47.5'

NOTE:

- Bottom heatsink (Pin 4) is electrically isolated from Pin 1, 2, or 3.
- This drawing will meet dimensional requirement of JEDEC SS Product Outline TO-273 except D and D1 dimension.

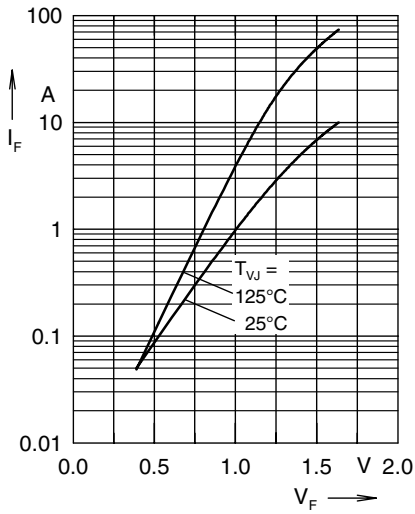


Fig. 1 typ. forward characteristics

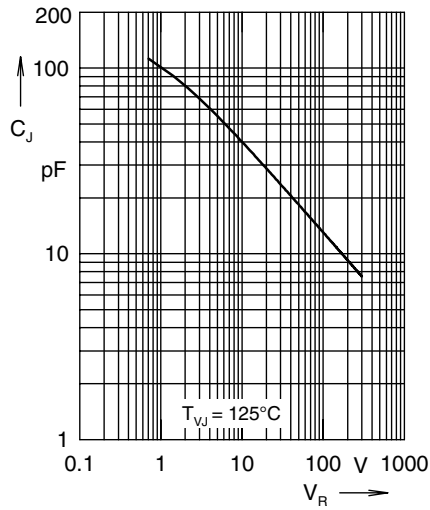


Fig. 2 typ. junction capacity versus blocking voltage

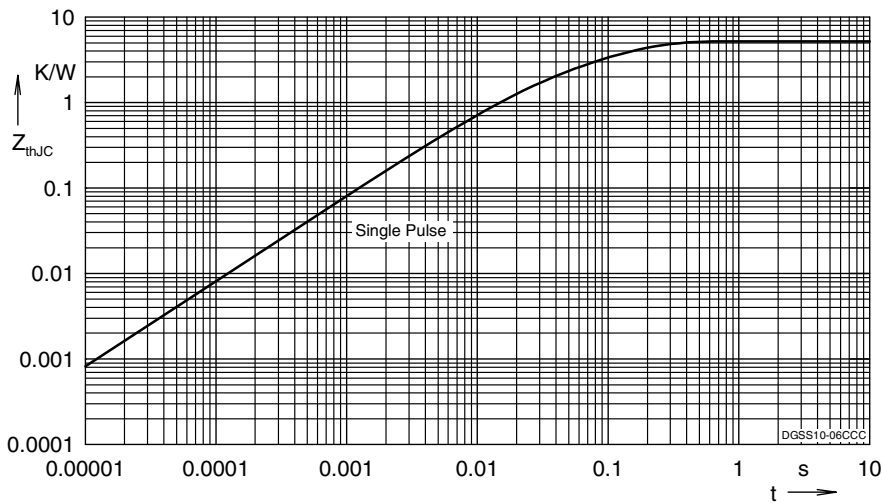


Fig. 3 typ. thermal impedance junction to case